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QUERY CONTROL FORM				RTIS USE ONLY	
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JACKET			
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b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
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SPECIFICATION

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g. Brief Description
h. Sequence Listing
i. Appendix
j. Amendments
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CLAIMS

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MESSAGE

On Page 12, Line 16 make a reference to a Figure 1. Should it read Figure 1A.

Please verify

Thank You

initials TW

RESPONSE Yes.

initials dlp

E-5 (Rev. 10/01/02)

determining, from said frequency spectrum, layer properties of layers on said part product.

Preferably, said property is one of a group comprising a thickness and a refractive index.

Preferably, said part product includes at least one at least partly transparent layer and said reflections include reflections from an upper and a lower surface of said at least partly transparent layer.

Preferably, said converting comprises producing said spectrum by Fourier transform of said analyzed intensities.

Brief Description of the Drawings

For a better understanding of the invention and to show how the same may be carried into effect, reference will now be made, purely by way of example, to the accompanying drawings, in which:

Fig. 1A is a simplified diagram of a layered wafer product,

Fig. 1B is a simplified diagram of the layered wafer product of Fig. 1A at a later stage in the production process,

Fig. 2 is a simplified ray diagram illustrating how light reflection can be used to obtain information of layer thicknesses in a layered wafer product,

Fig. 3 is a simplified schematic diagram of a reflection-based measuring device associated with a spinner in a semiconductor wafer production line,